

Amendments to the Claims

Claim 1 (**Currently Amended**) A semiconductor device comprising:
a semiconductor element including an electrode formed on an electrode-formed surface thereof;
a reinforcing member bonded to a back surface of said semiconductor element, said back surface being opposite to said electrode-formed surface; and
an adhesive bonding said semiconductor element and said reinforcing member while allowing said semiconductor element to be deformed,
wherein said reinforcing member has a flexural rigidity greater than a flexural rigidity of said semiconductor element.

Claim 2 (**Original**) The semiconductor device of claim 1, wherein said adhesive is made of resin having a low elastic modulus, and bonds said back surface of said semiconductor element entirely to said reinforcing member.

Claim 3 (**Original**) The semiconductor device of claim 1, wherein said adhesive bonds only a center of said back surface of said semiconductor element to said reinforcing member.

Claim 4 (**Canceled**)

Claim 5 (**Original**) The semiconductor device of claim 1, wherein said reinforcing member is larger than said semiconductor element in outside shape.

Claim 6 (**Original**) The semiconductor device of claim 5, wherein said reinforcing member includes:

a recess portion to which said semiconductor element is bonded; and
a projection formed at a border of said recess portion.

Claim 7 (**Original**) The semiconductor device of claim 1, wherein said reinforcing member functions as a holding member in handling.

Claim 8 (**Previously Presented**) The semiconductor device of claim 1, wherein identification information is applied to an applied surface of said reinforcing member, said applied surface being opposite to a surface of said reinforcing member bonded to said semiconductor element.

Claim 9 (**Canceled**)

Claim 10 (**Currently Amended**) A The method of ~~claim 9~~, manufacturing a semiconductor device, said method comprising:

shaving a back surface of a semiconductor wafer, the back surface being opposite to an electrode-formed surface of the semiconductor wafer including a plurality of semiconductor elements therein;

bonding a reinforcing plate to the shaved back surface of the semiconductor wafer with an adhesive; and

dividing the semiconductor wafer to which the reinforcing plate is bonded and the reinforcing plate into units of the semiconductor elements, the reinforcing plate being operable to be held by a mounting head when the semiconductor elements are being mounted to a substrate,

wherein said dividing of the semiconductor wafer and the reinforcing plate comprises dividing the reinforcing plate with a dicing width smaller than a dicing width of the semiconductor wafer.

Claim 11 (**Previously Presented**) A The method of ~~claim 9~~, further comprising manufacturing a semiconductor device, said method comprising:

shaving a back surface of a semiconductor wafer, the back surface being opposite to an electrode-formed surface of the semiconductor wafer including a plurality of semiconductor elements therein;

bonding a reinforcing plate to the shaved back surface of the semiconductor wafer with an adhesive;

dividing the semiconductor wafer to which the reinforcing plate is bonded and the reinforcing plate into units of the semiconductor elements, the reinforcing plate being operable to be held by a mounting head when the semiconductor elements are being mounted to a substrate; and

attaching a sheet to the electrode-formed surface of the semiconductor wafer, wherein said shaving of the back surface of the semiconductor wafer comprises shaving the back surface of the semiconductor wafer while the sheet is attached to the electrode-formed surface of the semiconductor wafer.

Claim 12 (**Currently Amended**) The method of claim 10 9, further comprising forming a bump on the electrode-formed surface of the semiconductor wafer.

Claim 13 (**Previously Presented**) A method of manufacturing a semiconductor device, said method comprising:

forming a diced groove along a border between a plurality of semiconductor elements from an electrode-formed surface of a semiconductor wafer which includes the semiconductor elements formed therein;

attaching a sheet to the electrode-formed surface of the semiconductor wafer having the diced groove;

dividing the semiconductor wafer into the semiconductor elements by shaving a back surface of the semiconductor wafer to thin the semiconductor wafer to a thickness until the shaved back surface reaches the diced groove, the back surface being opposite to the electrode-formed surface to which the sheet is attached;

bonding a reinforcing plate to the back surface of the semiconductor elements with an adhesive; and

dividing the reinforcing plate into units corresponding to the semiconductor elements after removing the sheet from the electrode-formed surface.

Claim 14 (**Previously Presented**) The method of claim 13, wherein said dividing of the reinforcing plate comprises dividing the reinforcing plate with a dicing width smaller than the diced groove of the semiconductor wafer.

Claim 15 (**Currently Amended**) A method of manufacturing a semiconductor device, said method comprising:

shaving a back surface of a semiconductor wafer, the back surface being opposite to an electrode-formed surface of the semiconductor wafer which includes a plurality of semiconductor elements;

dividing the semiconductor wafer into the semiconductor elements; ~~and~~

bonding a reinforcing member to a back surface of each of the semiconductor elements with an adhesive, the reinforcing member being operable to be held by a mounting head when the semiconductor elements are being mounted to a substrate; and

attaching a sheet to the electrode-formed surface of the semiconductor wafer, wherein said shaving of the back surface of the semiconductor wafer comprises shaving the back surface of the semiconductor wafer to which the sheet is attached.

Claim 16 (**Canceled**)

Claim 17 (**Previously Presented**) The method of claim 15, further comprising forming a bump on the electrode-formed surface of the semiconductor wafer.

Claim 18 (**Currently Amended**) A method of mounting a semiconductor device which includes:

a semiconductor element having an electrode-formed surface;

a reinforcing member bonded to a back surface of the semiconductor element that allows the semiconductor element to be deformed, the back surface being opposite the electrode-formed surface; and

an adhesive bonding the semiconductor element to the reinforcing member,

wherein said reinforcing member has a flexural rigidity greater than a flexural rigidity of said semiconductor element,

said method comprising:
holding the reinforcing member; and
mounting the semiconductor device to a workpiece, the semiconductor device having the reinforcing member held.

Claim 19 (**Previously Presented**) The method of claim 18,
wherein the reinforcing member includes a recess portion to which the semiconductor element is bonded and a projection formed at a border of the recess portion, and
wherein said mounting of the semiconductor device comprises bonding the projection to the workpiece.

Claim 20 (**Previously Presented**) The semiconductor device of claim 1, wherein said semiconductor element has a thickness not greater than $100\mu\text{m}$.

Claim 21 (**Currently Amended**) The method of claim 109, wherein said shaving of the back surface of the semiconductor wafer comprises shaving the back surface of the semiconductor wafer until the semiconductor wafer has a thickness of not greater than $100\mu\text{m}$.

Claim 22 (**Previously Presented**) The method of claim 13, wherein said shaving of the back surface of the semiconductor wafer comprises shaving the back surface of the semiconductor wafer until the semiconductor wafer has a thickness of not greater than $100\mu\text{m}$.

Claim 23 (**Previously Presented**) The method of claim 15, wherein said shaving of the back surface of the semiconductor wafer comprises shaving the back surface of the semiconductor wafer until the semiconductor wafer has a thickness of not greater than $100\mu\text{m}$.

Claim 24 (**Previously Presented**) The method of claim 18, wherein the semiconductor element has a thickness of not greater than $100\mu\text{m}$.

Claim 25 (**New**) The method of claim 11, further comprising forming a bump on the electrode-formed surface of the semiconductor wafer.

Claim 26 (**New**) The method of claim 11, wherein said shaving of the back surface of the semiconductor wafer comprises shaving the back surface of the semiconductor wafer until the semiconductor wafer has a thickness of not greater than $100\mu\text{m}$.